

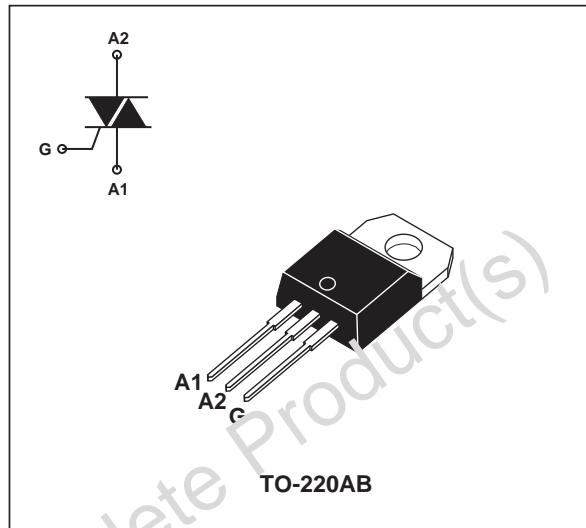
## SENSITIVE GATE TRIACS

### FEATURES

- Very low  $I_{GT}$  = 10mA max
- Low  $I_H$  = 15mA max
- BTA Family:  
Insulating voltage = 2500V<sub>(RMS)</sub>  
(UL recognized: E81734)

### DESCRIPTION

The BTA/BTB04 T/D/S/A triac family are high performance glass passivated PNPN devices. These parts are suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	BTA	$T_c = 90^\circ\text{C}$	4	A
		BTB	$T_c = 95^\circ\text{C}$		
$I_{TSM}$	Non repetitive surge peak off-state current ( $T_j$ initial = 25°C)		$t_p = 8.3\text{ms}$	42	A
			$t_p = 10\text{ms}$		
$I^2t$	$I^2t$ value		$t_p = 10\text{ms}$	8	$\text{A}^2\text{s}$
$dI/dt$	Critical rate of rise of on-state current Gate supply: $I_G = 50\text{mA}$ $dI_G/dt = 0.1\text{A}/\mu\text{s}$		Repetitive $F = 50\text{Hz}$	10	$\text{A}/\mu\text{s}$
			Non repetitive		
$T_{stg}$ $T_j$	Storage and operating junction temperature range			-40 to +150 -40 to +110	°C
$T_f$	Maximum lead soldering temperature during 10s at 4.5mm from case			260	°C

Symbol	Parameter	BTA / BTB04-			Unit
		400 T/D/S/A	600 T/D/S/A	700 T/D/S/A	
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage $T_j = 110^\circ\text{C}$	400	600	700	V

## BTA04 T/D/S/A BTB04 T/D/S/A

### THERMAL RESISTANCE

Symbol	Parameter	Value		Unit
R <sub>th</sub> (j-a)	Junction to ambient	60		°C/W
R <sub>th</sub> (j-c) DC	Junction to case for DC	BTA	4.4	°C/W
		BTB	3.2	
R <sub>th</sub> (j-c) AC	Junction to case for 360° conduction angle (F = 50Hz)	BTA	3.3	°C/W
		BTB	2.4	

### GATE CHARACTERISTICS (maximum values)

P<sub>G(AV)</sub> = 1W P<sub>GM</sub> = 40W (tp = 20μs) I<sub>GM</sub> = 4A (tp = 20μs) V<sub>GM</sub> = 16V (tp = 20μs)

### ELECTRICAL CHARACTERISTICS

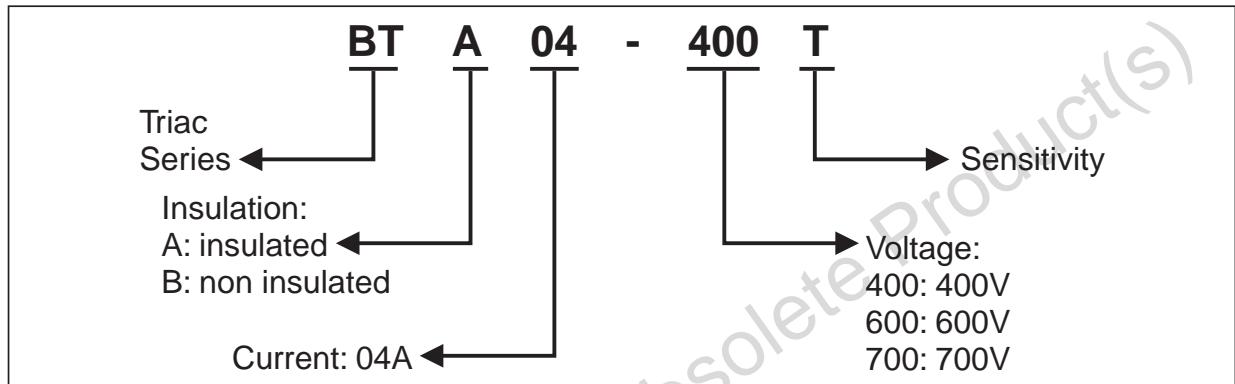
Symbol	Test conditions	Quadrant	BTA / BTB04				Unit	
			T	D	S	A		
I <sub>GT</sub>	V <sub>D</sub> = 12V (DC) R <sub>L</sub> = 33Ω	T <sub>j</sub> = 25°C	I - II - III	MAX.	5	5	10	mA
			IV	MAX.	5	10	10	
V <sub>GT</sub>	V <sub>D</sub> = 12V (DC) R <sub>L</sub> = 33Ω	T <sub>j</sub> = 25°C	I - II - III - IV	MAX.	1.5			V
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3kΩ	T <sub>j</sub> = 110°C	I - II - III - IV	MIN.	0.2			V
t <sub>gt</sub>	V <sub>D</sub> = V <sub>DRM</sub> I <sub>G</sub> = 40mA dI <sub>G</sub> /dt = 0.5A/μs	T <sub>j</sub> = 25°C	I - II - III - IV	TYP.	2			μs
I <sub>L</sub>	I <sub>G</sub> = 1.2I <sub>GT</sub>	T <sub>j</sub> = 25°C	I - III - IV	TYP.	10	10	20	mA
			II		20	20	40	
I <sub>H</sub> *	I <sub>T</sub> = 100mA Gate open	T <sub>j</sub> = 25°C		MAX.	15	15	25	mA
V <sub>TM</sub> *	I <sub>TM</sub> = 5.5A tp = 380μs	T <sub>j</sub> = 25°C		MAX.	1.65			V
I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> rated V <sub>RRM</sub> rated	T <sub>j</sub> = 25°C		MAX.	0.01			mA
		T <sub>j</sub> = 110°C		MAX.	0.75			
dV/dt *	Linear slope up to V <sub>D</sub> = 67% V <sub>DRM</sub> gate open	T <sub>j</sub> = 110°C		TYP.	10	10	-	V/μs
				MIN.	-	-	10	
(dl/dt)c*	(dl/dt)c = 1.8A/ms	T <sub>j</sub> = 110°C		TYP.	1	1	5	5 V/μs

\* For either polarity of electrode A<sub>2</sub> voltage with reference to electrode A<sub>1</sub>

## PRODUCT INFORMATION

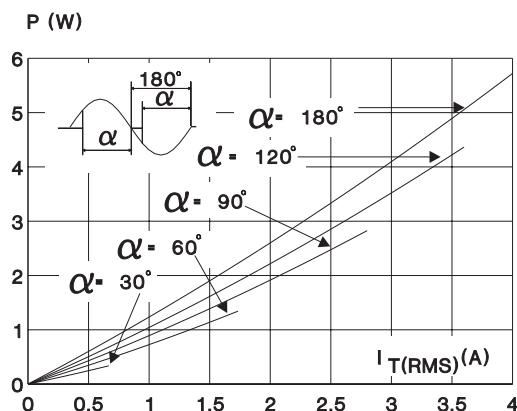
Package	$I_T(\text{RMS})$	$V_{\text{DRM}} / V_{\text{RRM}}$	Sensitivity Specification			
	A	V	T	D	S	A
BTA (Insulated)	4	400	X			X
		600	X	X		
		700	X		X	
	5	400	X	X		
		600	X		X	

## ORDERING INFORMATION

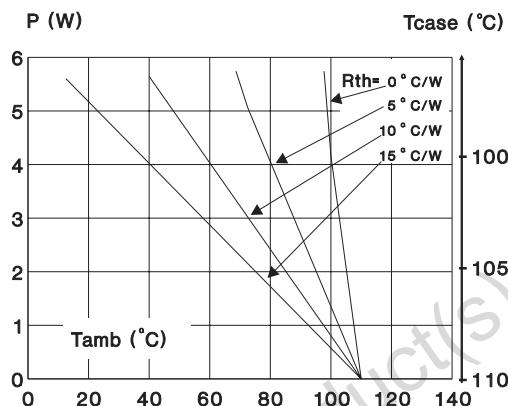


## BTA04 T/D/S/A    BTB04 T/D/S/A

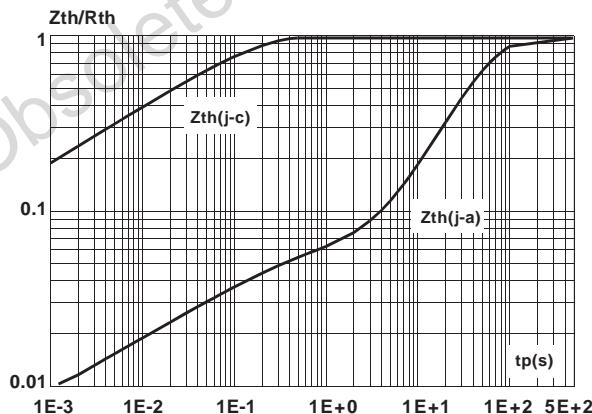
**Fig. 1:** Maximum RMS power dissipation versus RMS on-state current ( $F = 50\text{Hz}$ ). (Curves are cut off by  $(dI/dt)c$  limitation)



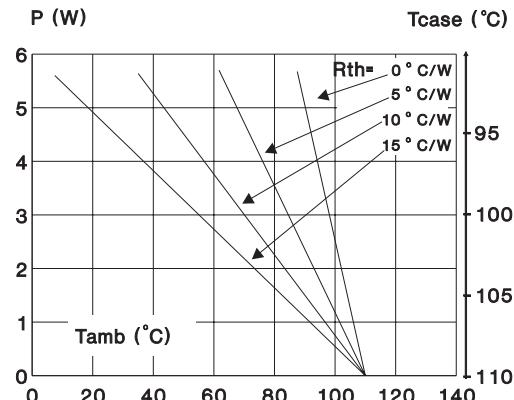
**Fig. 3:** Correlation between maximum RMS power dissipation and maximum allowable temperature ( $T_{\text{amb}}$  and  $T_{\text{case}}$ ) for different thermal resistances heatsink + contact (BTB).



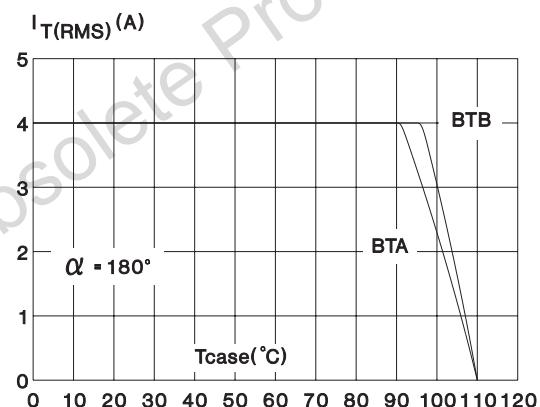
**Fig. 5:** Relative variation of thermal impedance versus pulse duration.



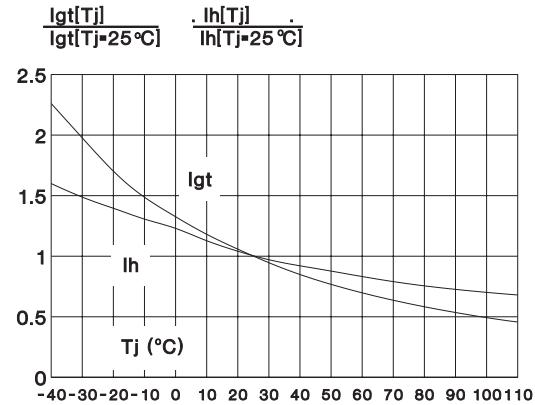
**Fig. 2:** Correlation between maximum RMS power dissipation and maximum allowable temperature ( $T_{\text{amb}}$  and  $T_{\text{case}}$ ) for different thermal resistances heatsink + contact (BTA).



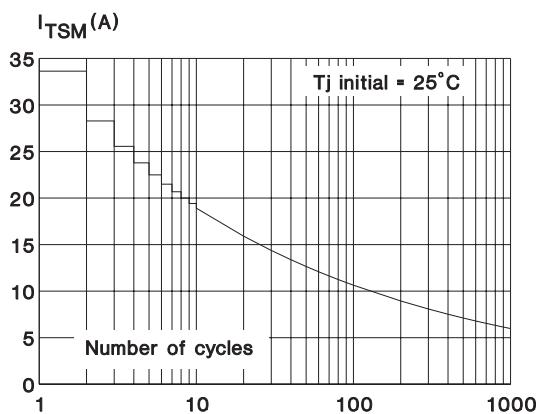
**Fig. 4:** RMS on-state current versus case temperature.



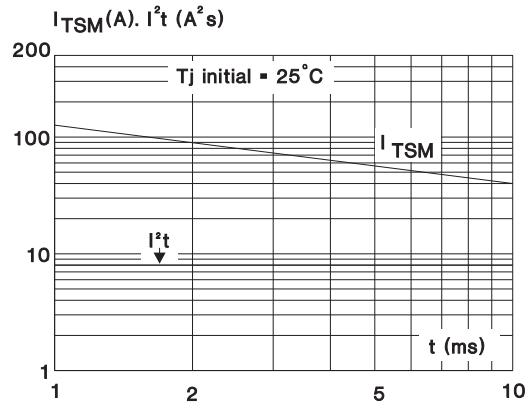
**Fig. 6:** Relative variation of gate trigger current and holding current versus junction temperature.



**Fig. 7:** Non repetitive surge peak on-state current versus number of cycles.



**Fig. 8:** Non repetitive surge peak on-state current for a sinusoidal pulse with width:  $t \leq 10\text{ms}$ , and corresponding value of  $I^2t$ .



**Fig. 9:** On-state characteristics (maximum values).

